

REMARKS

Claims 1 and 32-47 are pending in the present application.

The specification was amended to eliminate the footnotes and to correct various typographical and grammatical errors in the specification.

Claim 1 was amended and claims 32-47 were added for clarity and explication.

Examination of the application on the merits is respectfully requested.

AMENDMENTS WITH MARKINGS TO SHOW CHANGES MADE

A version of the substitute specification marked up to show all changes relative to the previous version of the specification is attached hereto.

Claim 1 was amended herein as follows:

1. (amended) An integrated circuit structure fabrication method, comprising[the steps of]:
- [(a) providing a substrate which includes at least one substantially monolithic body of a semiconductor material;
 - (b)] forming n-type and p-type regions [at a surface of said body]within a substrate;
 - [(c)] forming an oxidation barrier on [said]a surface of the substrate over the n-type and p-type regions;
 - [(d)] forming a first patterned layer which exposes [predetermined locations of]first isolation areas in [said]the n-type region[, and which covers substantially all of [said]the p-type region[s] and [predetermined locations of]active device areas in [said]the n-type region[s]; and thereafter
 - (d.1) etching away said]removing portions of the oxidation barrier layer [where] exposed by [said respective]the first patterned layer[, and] to expose the first isolation areas;
 - [(d.2)] implanting a first channel-stop dopant into the first isolation areas exposed by [said respective]the first patterned layer and the oxidation barrier layer;[, and
 - (d.3)] removing [said respective]the first patterned layer;
 - [(e)] forming a second patterned layer which exposes [predetermined locations of]second isolation areas in [said]the p-type region[, and which covers substantially all of [said]the n-type

18 region[s] and [predetermined locations of] active device areas in [said]the p-type region[s];
19 [and thereafter
20 (e.1) etching away said]removing portions of the oxidation barrier layer [where] exposed by [said
21 respective]the second patterned layer[, and]to expose the second isolation areas;
22 [(e.2)] implanting a second channel-stop dopant into the second isolation areas exposed by [said
23 respective]the second patterned layer and the oxidation barrier layer;[, and
24 (e.3)] removing [said respective]the second patterned layer; and
25 [(f)] growing a field oxide on [said body]the first and second isolation areas where exposed by
26 [said]the oxidation barrier layer in a single oxidation step.


If any outstanding issues remain, or if the Examiner has any further suggestions for expediting prosecution of this Application, the Applicant respectfully invites the Examiner to contact the undersigned at the telephone number indicated below or at *dvenglarik@novakov.com*.

Respectfully submitted,

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Date: 9-28-01

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